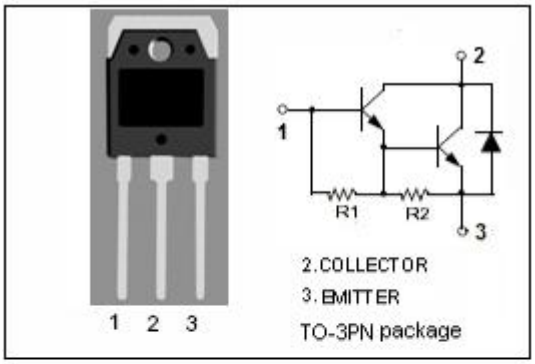
isc Silicon NPN Darlington Power Transistor 2SD1982



DESCRIPTION

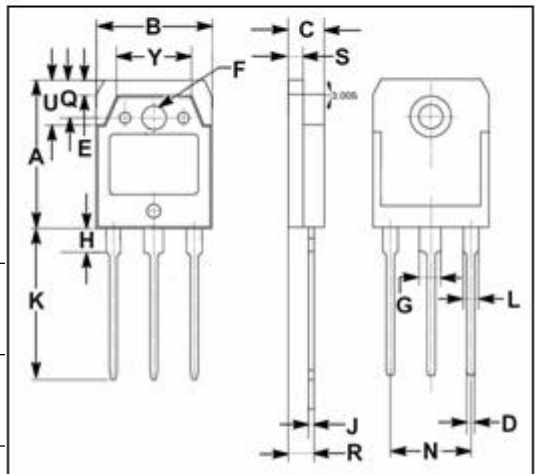
- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= 300V(Min)
- Low Collector Saturation Voltage
- High DC Current Gain
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Switching regulator
- General purpose power amplifiers

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	300	V
V_{CEO}	Collector-Emitter Voltage	300	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	6	A
P_C	Collector Power Dissipation @ T_C=25℃	80	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	19.60	20.30
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	19.80	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 10mA; I_B= 0	300			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C=1mA; I_E= 0	300			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 5mA; I_C= 0	5			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= 4A; I_B= 16mA			1.8	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C=6A; I_B= 24mA			2.0	V
$V_{BE(sat)-1}$	Base-Emitter Saturation Voltage	I_C= 4A; I_B= 16mA			2.0	V
$V_{BE(sat)-2}$	Base-Emitter Saturation Voltage	I_C=6A; I_B= 24mA			2.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 300V; I_E= 0			100	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			5.0	mA
h_{FE}	DC Current Gain	I_B= 4A; V_{CE}= 2V	2000			